

AN5290 Application note

Minimal BOM for STM32WB Series microcontrollers

Introduction

STM32WB Series microcontrollers are designed to minimize the number of external components needed to ensure optimized RF performance.

This document details the bill of materials (BOM) for Bluetooth® Low-Energy applications.

The QFN48 package is used as a reference but the considerations valid for it can easily be extended to other packages.

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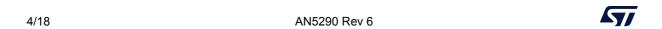


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1 Design considerations

1.1 SMPS and LDO configurations

The STM32WB Series microcontrollers are based on Arm[®](a) cores.

The power management implemented on some of these devices (see the datasheets available on www.st.com) embeds a powerful switched mode power supply (SMPS) to improve power efficiency when the supply voltage is higher than 2 V, otherwise the LDO configuration is used. The two configurations are shown in Figure 1. See AN5246 "Usage of SMPS on STM32WB Series microcontrollers", available on www.st.com, for more details.

 V_{DD} VDDSMPS VDDSMPS **SMPS SMPS** VLXSMPS VLXSMPS SMPS mode or (not used) BYPASS mode LPR LPR VFBSMPS VFBSMPS **RFR** MR **RFR** MR SMPS configuration LDO configuration MS41409V4

Figure 1. Supply configurations

To operate properly, the SMPS needs two inductors and two capacitors. In the LDO configuration no external components are needed. The detailed electrical schemes are shown in *Section 2*.

arm

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1.2 LDO configuration for $V_{DD} > 3 \text{ V}$

This configuration applies only to STM32WB55Vx devices with REV_ID = 0x2001 in register DBGMCU_IDCODE (see RM0434, available on www.st.com).

An inductance and a resistor must be added in series between VLXSMPS and VFBSMPS pins, as shown in *Figure 2*.

VDDSMPS

VLXSMPS

SMPS

(not used)

VFBSMPS

Main RF LP regulator regulator

Figure 2. LDO configuration

The recommended values (see Figure 3) are:

- Inductance: 1.8 ± 0.1 nH, 6 GHz ± 15% self-resonance frequency, 1000 mA rated current (e.g. Murata LQG15HS1N8B02)
- Resistor: 2.2 Ω, able to support 1 W for 5 ns (e.g. Vishay D10/CRCW0402e3)

VDDSMPS

C12

4.7uF

GND

C1

VDDSMPS

C1

VDDSMPS

C1

VDDSMPS

VLXSMPS

VFBSMPS

VFBSMPS

VSSSMPS

Figure 3. Recommended schematic for the no SMPS configurations (STM32WB55Vx)

1.3 HSE trimming

STM32WB MCUs use the HSE oscillator for the RF clock generation, this component must be fine-tuned. Internal load capacitors are used, removing the need for external parts, as shown in *Figure 4*. See AN5042 "HSE trimming for RF applications using the STM32WB Series", available on www.st.com, for more details.

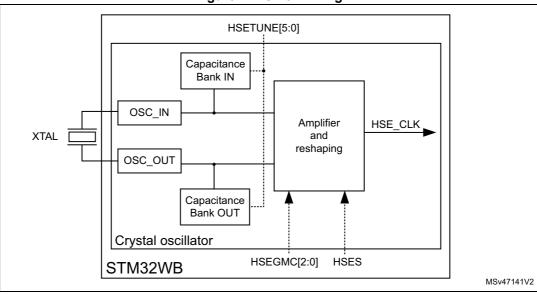


Figure 4. HSE trimming

1.4 RF matching

There is a unique pin RX/TX for the RF and this interface is single ended, thus eliminating the need for external baluns. Furthermore, internal band pre-filtering helps to reduce external components.

An external PI filter made-up by discrete components followed by a ceramic filter is needed for, respectively, impedance matching and harmonics rejection. Another matching network is required for the antenna. To optimize the BOM and the performance stability, these filters can be replaced by an internal passive device (IPD), as shown in *Figure 5*.

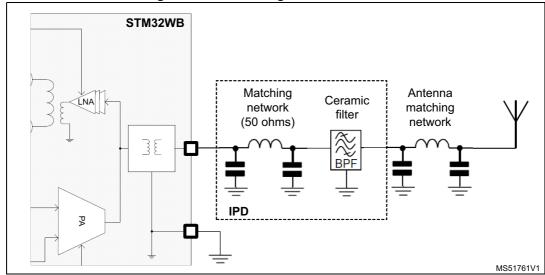


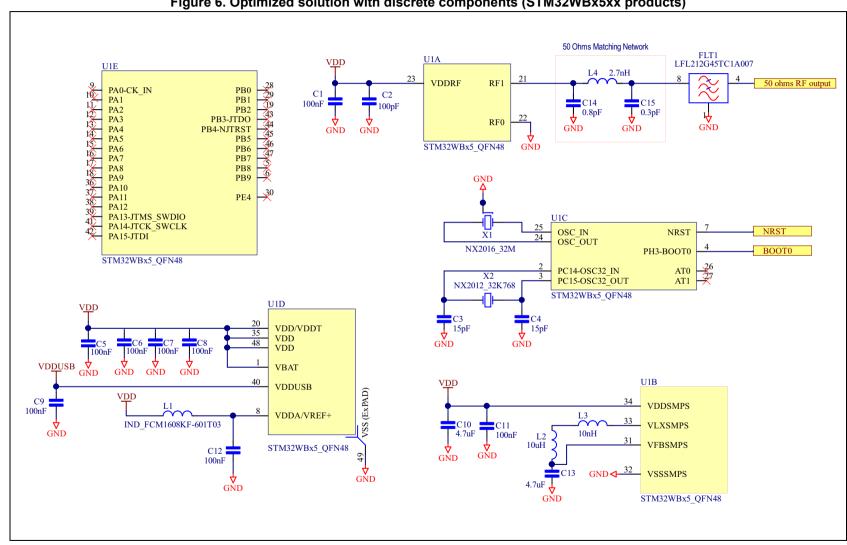
Figure 5. RF matching and external filters

The RF performance strongly depends upon the PCB layout. AN5165 "Development of RF hardware using STM32WB microcontrollers", available on www.st.com, describes the precautions to be taken for the layout of an RF board with the STM32WB.

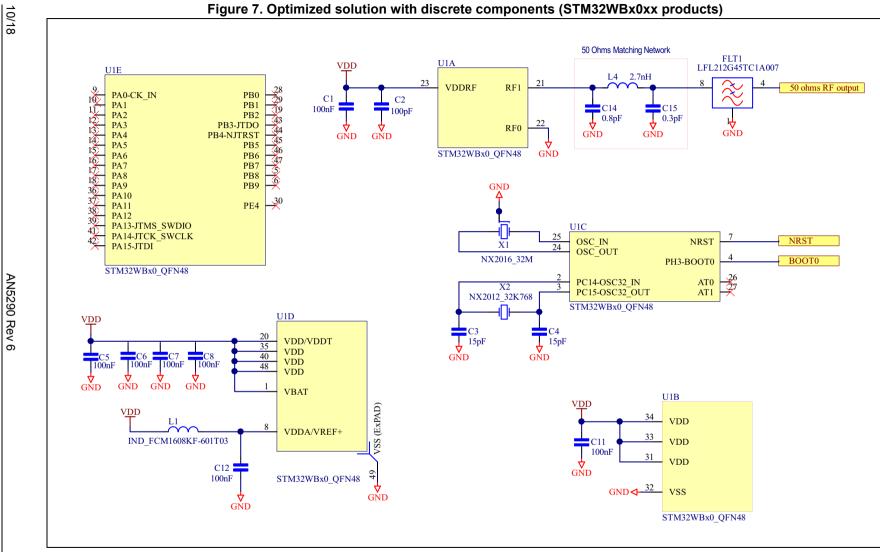
Schematics

Schematics

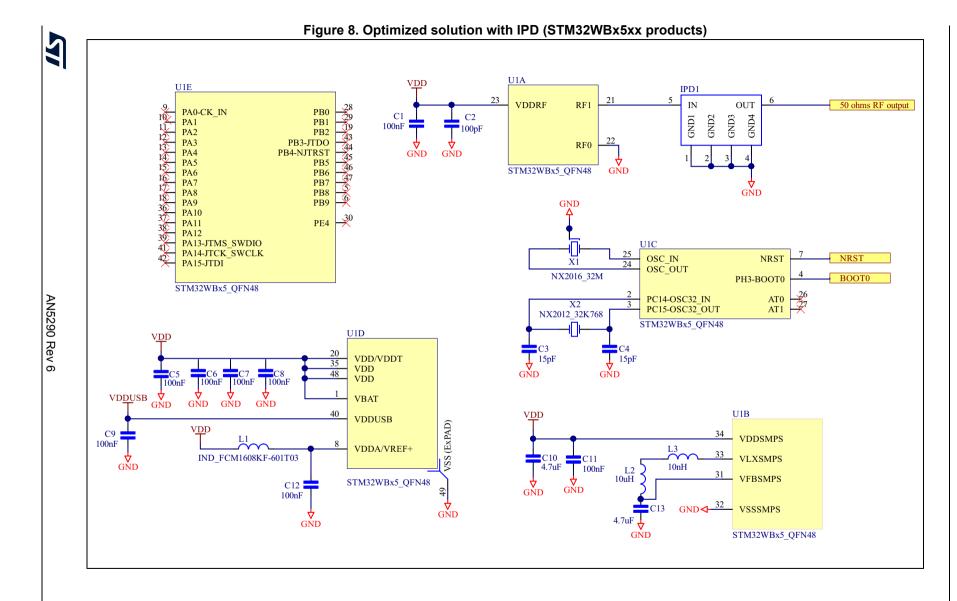
Figure 6. Optimized solution with discrete components (STM32WBx5xx products)

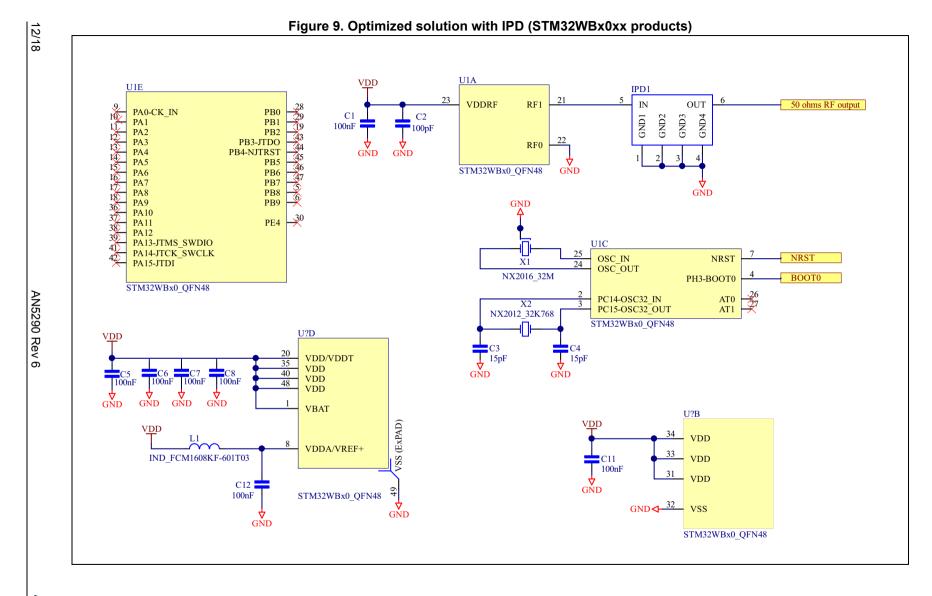


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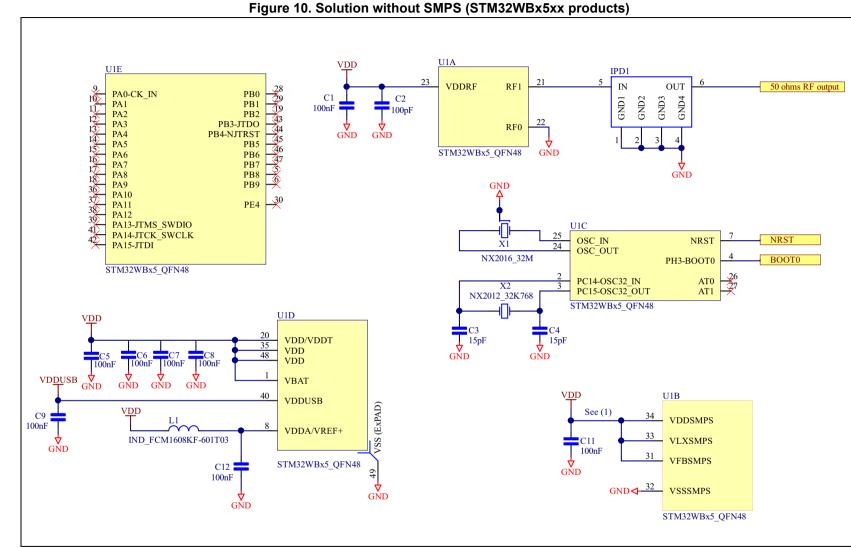












1. For STM32WB55Vx add L and R, as indicated in Section 1.2: LDO configuration for VDD > 3 V

Bill of materials AN5290

3 Bill of materials

Table 1. Bill of materials - Optimized solution with discrete components

| Designator | Description | Comment | Footprint | Manufacturer | Part number |
|--|--------------------------------|--------------------------------|------------------|--------------|--------------------|
| C1, C5, C6, C7, C8, C9, C11, C12 | Capacitor, not polarized (X5R) | 100 nF decoupling capacitors | | Murata | GRM155R61H104KE19D |
| C2 | | 100 pF decoupling capacitors | 0402 | Yageo | CC0402KRX7R9BB101 |
| C3, C4 | | 15 pF LSE crystal capacitor | | Murata | GRM1555C1H4R3CA01D |
| C10, C13 | Capacitor, not polarized | 4.7 µF decoupling capacitor | | | GRM155R61A475MEAAD |
| C14 | | 0.8 pF matching network | | | GRM1555C1HR80BA01D |
| C15 | | 0.3 pF matching network | | | GRM1555C1HR30WA01D |
| L1 | Coil | Filtering coil | 0603 | TAI-TECH | FCM1608KF-601T03 |
| L2 | Inductor | 10 µH SMPS inductor | 0805 | Murata | LQM21FN100M70L |
| L3 | | 10 nH SMPS inductor | 0402 | | LQG15WZ10NJ02D |
| L4 | | 2.7 nH matching network | | | LQG15HS2N7S02D |
| X1 | Crystal | 32 MHz - HSE | NX2016 NX2012 | NDK | NX2016SA_32MHz |
| X2 | Oi yotai | 32.768 kHz - LSE | | | NX2012SA_32-768kHz |
| FLT1 | Low-pass filter | Harmonics rejection | - | Murata | LFL212G45TC1A007 |

AN5290 Bill of materials

Table 2. Bill of materials- Optimized solution with IPD

| Designator | Description | Comment | Footprint | Manufacturer | Part number |
|--|--------------------------------|--------------------------------------|-----------------|--------------------|--------------------|
| C1, C5, C6, C7, C8, C9, C11, C12 | Capacitor, not polarized (X5R) | 100 nF decoupling capacitors | 0402 | Murata | GRM155R61H104KE19D |
| C2 | | 100 pF decoupling capacitors | | Yageo | CC0402KRX7R9BB101 |
| C3, C4 | Capacitor, not polarized | 15 pF LSE crystal capacitor | | Murata | GRM1555C1H4R3CA01D |
| C10, C13 | | 4.7 μF decoupling capacitor | | | GRM155R61A475MEAAD |
| L1 | Coil | Filtering coil | 0603 | TAI-TECH | FCM1608KF-601T03 |
| L2 | Inductor | 10 µH SMPS inductor | 0805 | Murata | LQM21FN100M70L |
| L3 | | 10 nH SMPS inductor | 0402 | | LQG15WZ10NJ02D |
| X1 | Cryotal | 32 MHz - HSE | NX2016 | NDK | NX2016SA_32MHz |
| X2 | Crystal | 32.768 kHz - LSE | NX2012 | | NX2012SA_32-768kHz |
| IPD1 | Integrated passive device | Matching network and low-pass filter | Bumpless CSP | STMicroelectronics | MLPF-WB55-01E3 |

Table 3. Bill of materials - Solution without SMPS

| Designator | Description | Comment | Footprint | Manufacturer | Part number |
|--|--|--------------------------------------|-----------------|--------------------|--------------------|
| C1, C5, C6, C7, C8, C9, C11, C12 | Capacitor, not polarized (X5R) Capacitor, not polarized | 100 nF decoupling capacitors | 0402 | Murata | GRM155R61H104KE19D |
| C2 | | 100 pF decoupling capacitors | | Yageo | CC0402KRX7R9BB101 |
| C3, C4 | | 15 pF LSE crystal capacitor | | Murata | GRM1555C1H4R3CA01D |
| L1 | Coil | Filtering coil | 0603 | TAI-TECH | FCM1608KF-601T03 |
| X1 | Crystal | 32 MHz - HSE | NX2016 | NDK | NX2016SA_32MHz |
| X2 | | 32.768 kHz - LSE | NX2012 | NDK | NX2012SA_32-768kHz |
| IPD1 | Integrated passive device | Matching network and low-pass filter | Bumpless CSP | STMicroelectronics | MLPF-WB55-01E3 |

Conclusion AN5290

4 Conclusion

The devices of the STM32WB Series show excellent RF performance (detailed in the product datasheets available on www.st.com), with a minimal set of external components associated with a PCB layout that complies with RF guidelines.

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AN5290 Revision history

5 Revision history

Table 4. Document revision history

| Date | Revision | Changes | |
|---|----------|---|--|
| 14-Feb-2019 | 1 | Initial release. | |
| 20-Feb-2019 | 2 | Updated Section 1.1: SMPS and LDO configurations. Updated Table 2: Bill of materials- Optimized solution with IPD. | |
| 25-Sep-2019 | 3 | Updated Section 1.1: SMPS and LDO configurations and Section 4: Conclusion. Updated Figure 4: HSE trimming, Figure 6: Optimized solution with discrete components (STM32WBx5xx products), Figure 8: Optimized solution with IPD (STM32WBx5xx products) and Figure 10: Solution without SMPS (STM32WBx5xx products). Added Figure 7: Optimized solution with discrete components (STM32WBx0xx products) and Figure 9: Optimized solution with IPD (STM32WBx0xx products). | |
| 22-Jan-2020 | 4 | Updated Table 1: Bill of materials - Optimized solution with discrete components, Table 2: Bill of materials - Optimized solution with IPD and Table 3: Bill of materials - Solution without SMPS. Updated Figure 6: Optimized solution with discrete components (STM32WBx5xx products), Figure 7: Optimized solution with discrete components (STM32WBx0xx products), Figure 8: Optimized solution with IPD (STM32WBx5xx products), Figure 9: Optimized solution with IPD (STM32WBx0xx products) and Figure 10: Solution without SMPS (STM32WBx5xx products). | |
| 12-May-2020 | 5 | Updated Figure 1: Supply configurations. Added Section 1.2: LDO configuration for VDD > 3 V. | |
| Updated Figure 3: Recommended schematic for configurations (STM32WB55Vx). | | Added footnote to Figure 10: Solution without SMPS (STM32WBx5xx | |

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